

ABSTRACT OF THE DISCLOSURE

To provide a transistor having sufficient dielectric strength, including a gate insulating film which can be formed by easy processes, and not requiring a high-temperature crystallizing process, a method of manufacturing the transistor, and an electro-optical device, a semiconductor device, and an electronic apparatus including the transistor, a transistor includes at least a monocrystalline semiconductor layer and a gate insulating film provided on the monocrystalline semiconductor layer. The gate insulating film has a thermal oxide film formed on the monocrystalline semiconductor layer, and at least one vapor-deposited insulating film formed on the thermal oxide film.